# P-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|---|---|---|---|
| $V_{DS}$ (V) | $R_{DS(on)}$ (Ω) | $I_D$ (A)[a, b] | $Q_g$ (Typ.) |
| - 30 | 0.088 at $V_{GS}$ = - 10 V | - 2.7 | 4.1 nC |
| | 0.130 at $V_{GS}$ = - 4.5 V | - 2.2 | |

## FEATURES

- DT-Trench Power MOSFET

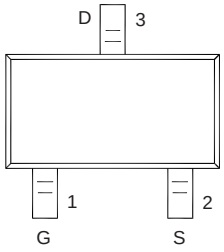
## APPLICATIONS

- Load Switch for Portable Devices

Pb-free

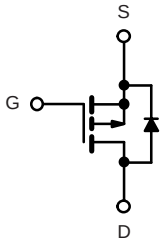
RoHS COMPLIANT

**(SOT-23-3L)**




Top View

DTS3401




P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS $T_A$ = 25 °C, unless otherwise noted | | | | |
|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Limit** | **Unit** |
| Drain-Source Voltage | | $V_{DS}$ | - 30 | V |
| Gate-Source Voltage | | $V_{GS}$ | ± 20 | |
| Continuous Drain Current ($T_J$ = 150 °C)[a, b] | $T_C$ = 25 °C | $I_D$ | - 3.5 | A |
| | $T_C$ = 70 °C | | - 2.8 | |
| | $T_A$ = 25 °C | | - 2.7[a, b] | |
| | $T_A$ = 70 °C | | - 2.2[a, b] | |
| Pulsed Drain Current (10 µs Pulse Width) | | $I_{DM}$ | - 12 | |
| Continuous Source-Drain Diode Current[a, b] | $T_C$ = 25 °C | $I_S$ | - 1.5 | |
| | $T_A$ = 25 °C | | - 0.91[a, b] | |
| Maximum Power Dissipation[a, b] | $T_C$ = 25 °C | $P_D$ | 1.8 | W |
| | $T_C$ = 70 °C | | 1.14 | |
| | $T_A$ = 25 °C | | 1.1[a, b] | |
| | $T_A$ = 70 °C | | 0.7[a, b] | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | - 55 to 150 | °C |
| Soldering Recommendations (Peak Temperature)[c] | | | 260 | |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Typical** | **Maximum** | **Unit** |
| Maximum Junction-to-Ambient[a, c] | t ≤ 5 s | $R_{thJA}$ | 90 | 115 | °C/W |
| Maximum Junction-to-Foot (Drain) | Steady State | $R_{thJF}$ | 55 | 70 | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. t = 5 s.

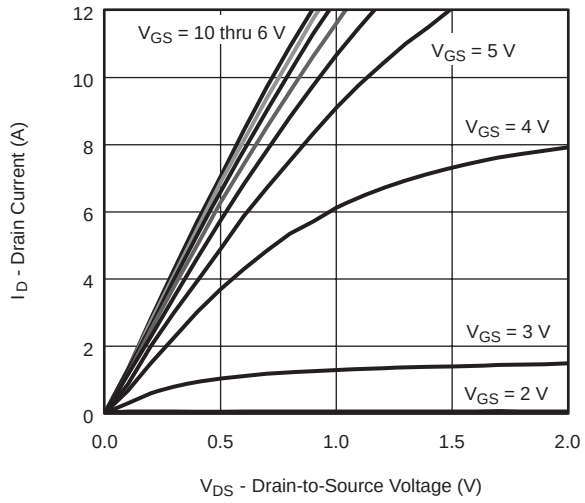
c. Maximum under Steady State conditions is 166 °C/W.

| **SPECIFICATIONS** $T_J$ = 25 °C, unless otherwise noted | | | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Conditions** | **Min.** | **Typ.** | **Max.** | **Unit** |
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = - 250 µA | - 30 | | | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D$ = - 250 µA | | - 32 | | mV/°C |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | 4.5 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = - 250 µA | - 1 | | - 3 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V | | | - 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = - 30 V, $V_{GS}$ = 0 V | | | - 1 | µA |
| | | $V_{DS}$ = - 30 V, $V_{GS}$ = 0 V, $T_J$ = 55 °C | | | - 10 | |
| On-State Drain Current[a] | $I_{D(on)}$ | $V_{DS} \leq$ 5 V, $V_{GS}$ = - 10 V | - 6 | | | A |
| Drain-Source On-State Resistance[a] | $R_{DS(on)}$ | $V_{GS}$ = - 10 V, $I_D$ = - 3.5 A | | 0.073 | 0.088 | Ω |
| | | $V_{GS}$ = - 4.5 V, $I_D$ = - 2.5 A | | 0.110 | 0.138 | |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = - 10 V, $I_D$ = - 3.5 A | | 7 | | S |
| **Dynamic[b]** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$ = - 15 V, $V_{GS}$ = 0 V, f = 1 MHz | | 340 | | pF |
| Output Capacitance | $C_{oss}$ | | | 67 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 51 | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = - 15 V, $V_{GS}$ = - 4.5 V, $I_D$ = - 2.5 A | | 4.1 | 6.2 | nC |
| Gate-Source Charge | $Q_{gs}$ | | | 1.3 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 1.8 | | |
| Gate Resistance | $R_g$ | f = 1 MHz | | 10 | | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = - 15 V, $R_L$ = 15 Ω<br>$I_D \cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 Ω | | 40 | 60 | ns |
| Rise Time | $t_r$ | | | 40 | 60 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 20 | 40 | |
| Fall Time | $t_f$ | | | 17 | 30 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = - 15 V, $R_L$ = 15 Ω<br>$I_D \cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 Ω | | 5.5 | 10 | |
| Rise Time | $t_r$ | | | 13 | 25 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 17 | 30 | |
| Fall Time | $t_f$ | | | 7.7 | 15 | |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | $T_C$ = 25 °C | | | - 1.5 | A |
| Pulse Diode Forward Current | $I_{SM}$ | | | | - 12 | |
| Body Diode Voltage | $V_{SD}$ | $I_S$ = - 0.75 A, $V_{GS}$ = 0 V | | - 0.8 | - 1.2 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $I_F$ = - 2.5 A, dI/dt = 100 A/µs, $T_J$ = 25 °C | | 17 | 30 | ns |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | | 11 | 20 | nC |
| Reverse Recovery Fall Time | $t_a$ | | | 12 | | ns |
| Reverse Recovery Rise Time | $t_b$ | | | 5 | | |

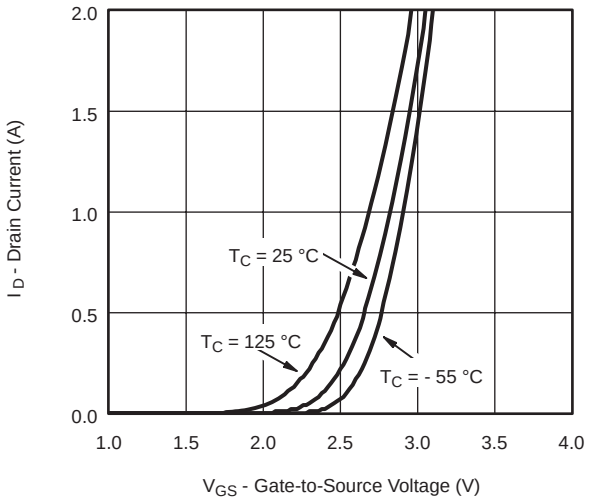
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

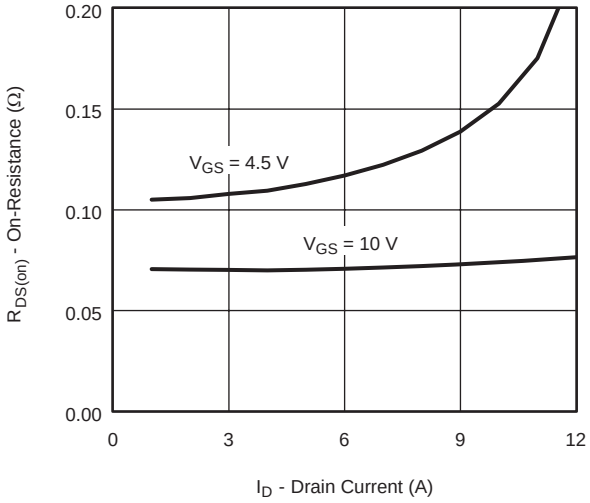
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



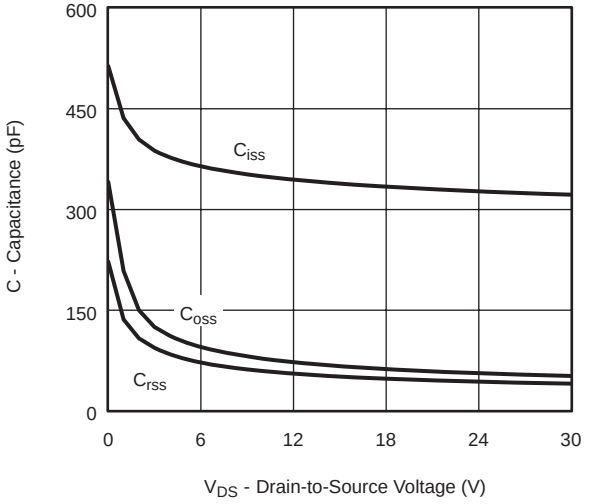

**Output Characteristics**



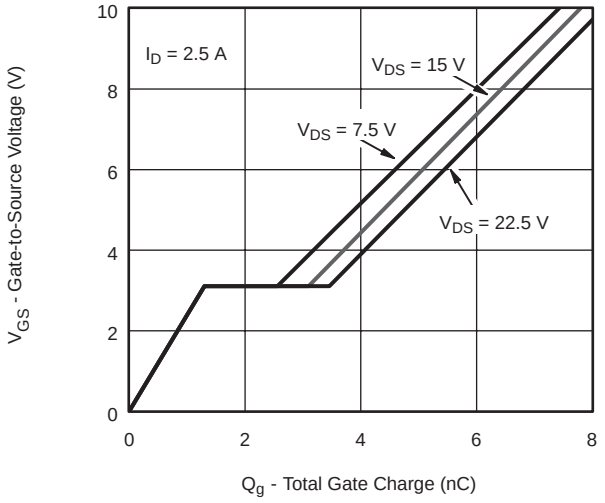

**Transfer Characteristics**



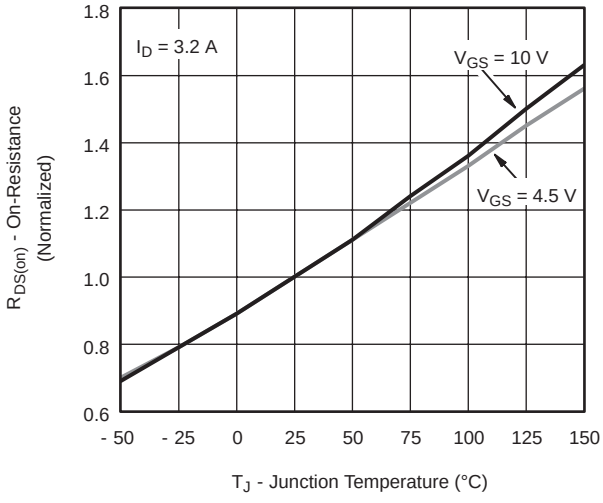

**On-Resistance vs. Drain Current and Gate Voltage**




**Capacitance**

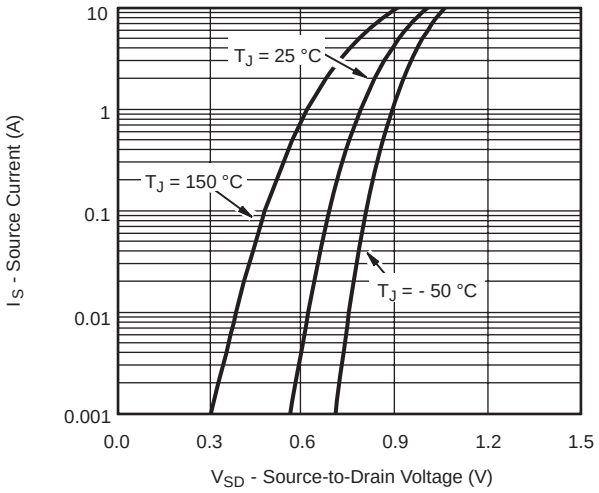



**Gate Charge**

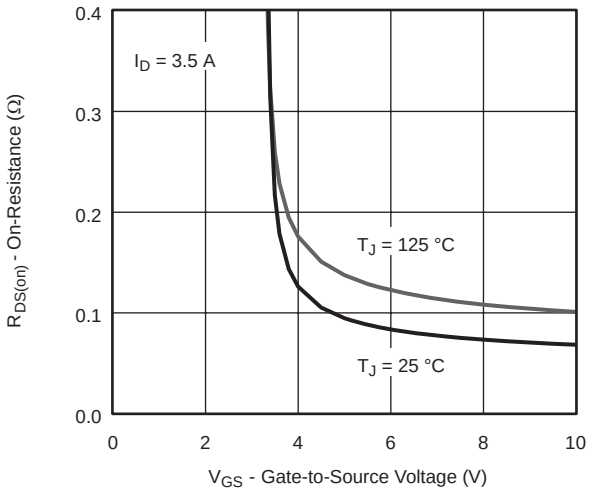



**On-Resistance vs. Junction Temperature**

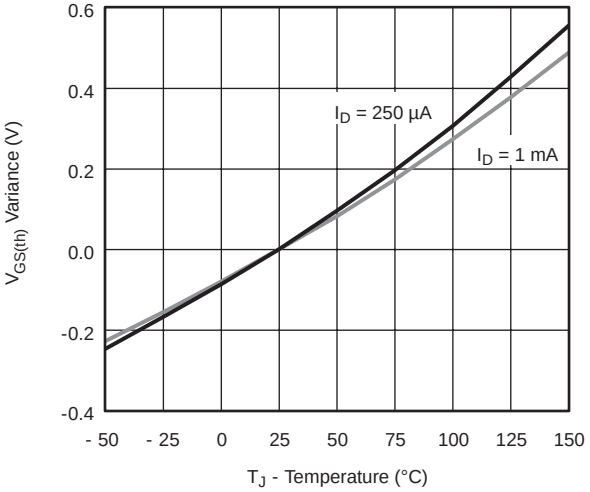
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



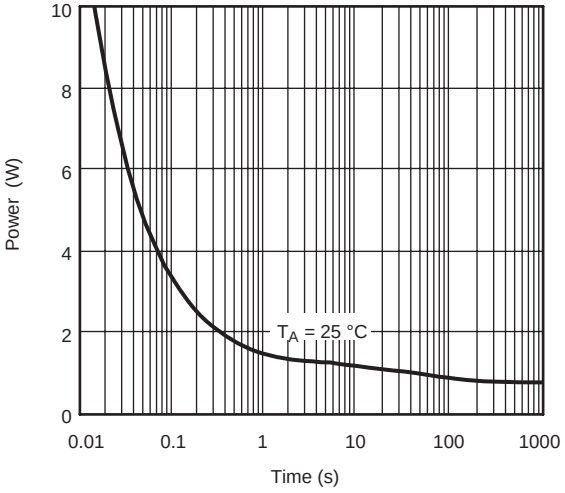

**Source-Drain Diode Forward Voltage**



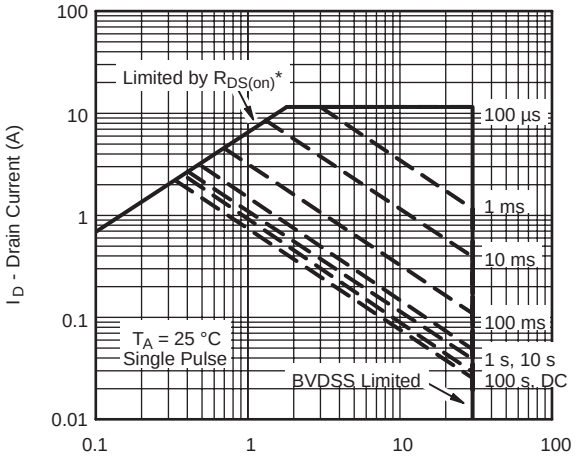

**On-Resistance vs. Gate-to-Source Voltage**




**Threshold Voltage**



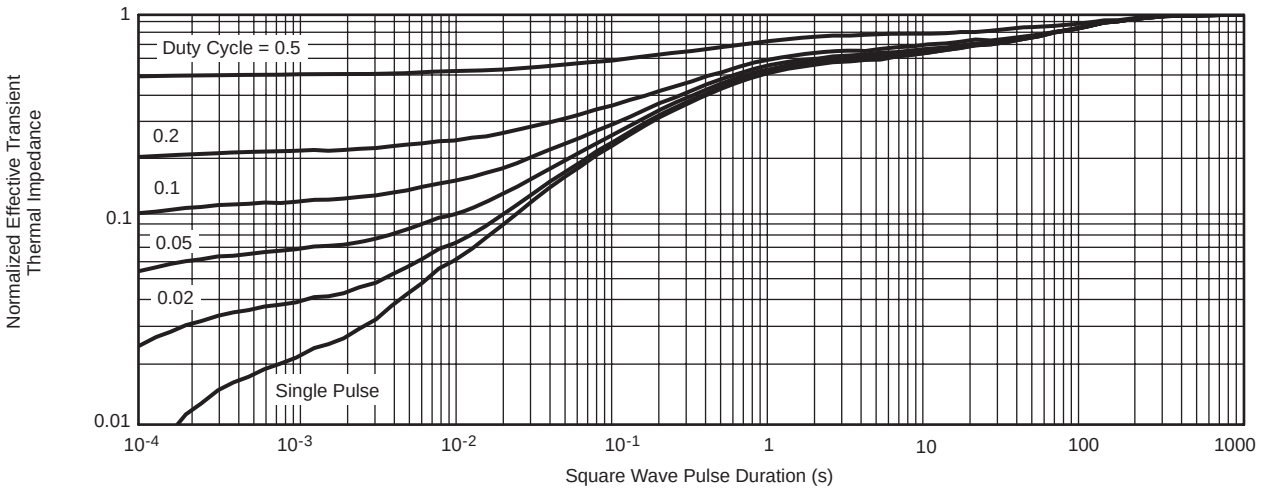

**Single Pulse Power, Junction-to-Ambient**

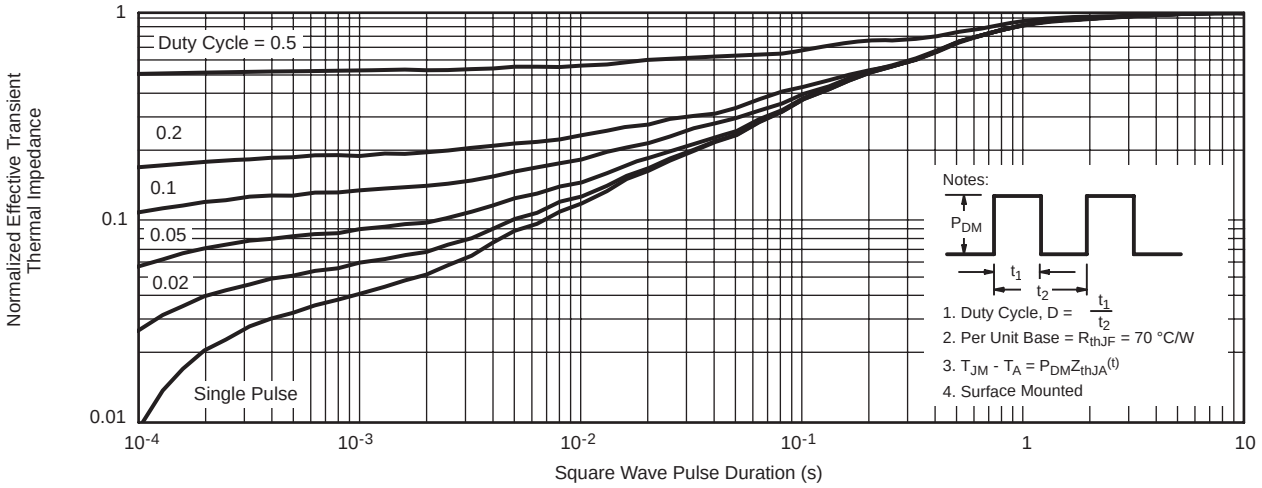



* $V_{GS}$ > minimum $V_{GS}$ at which $R_{DS(on)}$ is specified

**Safe Operating Area, Junction-to-Ambient**

**THERMAL RATINGS** ($T_A$ = 25 °C, unless otherwise noted)



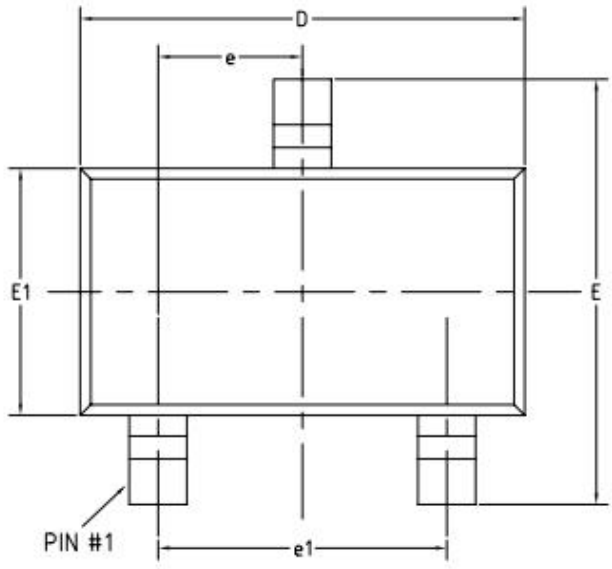

**Normalized Thermal Transient Impedance, Junction-to-Foot**

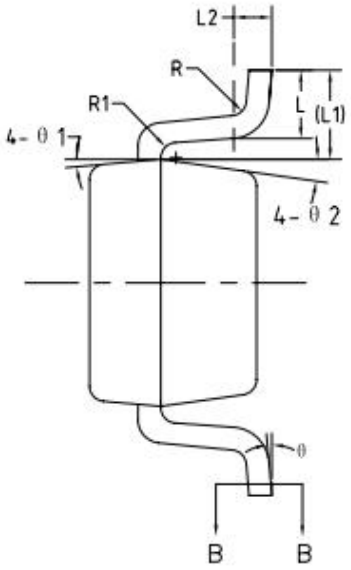
**Note**

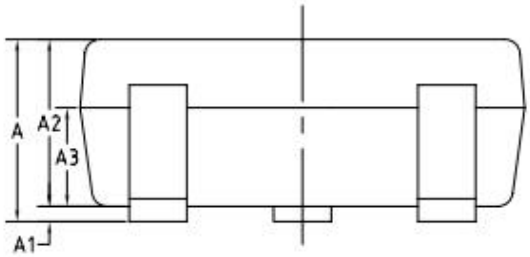
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 ℃ )

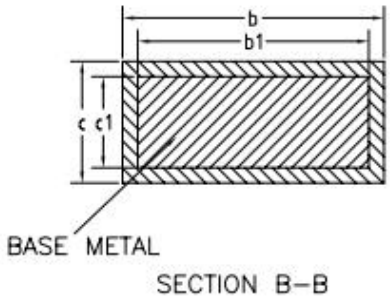
  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOT-23-3L PACKAGE OUTLINE




SECTION B–B

COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

| SYMBOL | MIN | TYP | MAX |
|---|---|---|---|
| A | - | - | 1.50 |
| A1 | 0.00 | - | 0.18 |
| A2 | 0.85 | 1.10 | 1.35 |
| A3 | 0.58 | 0.65 | 0.72 |
| b | 0.23 | - | 0.53 |
| b1 | 0.20 | 0.40 | 0.50 |
| c | 0.09 | - | 0.22 |
| c1 | 0.08 | 0.13 | 0.21 |
| D | 2.78 | 2.95 | 3.10 |
| E | 2.58 | 2.80 | 3.03 |
| E1 | 1.55 | 1.65 | 1.78 |
| e | 0.83 | 0.95 | 1.07 |
| e1 | 1.78 | 1.90 | 2.02 |
| L | 0.28 | 0.45 | 0.62 |
| L1 | 0.59REF | | |
| L2 | 0.25BSC | | |
| R | 0.04 | - | - |
| R1 | 0.04 | - | 0.21 |
| θ | 0° | - | 8° |
| θ 1 | 8° | 10° | 12° |
| θ 2 | 8° | 10° | 12° |

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